

11 Conclusion

Under Construction

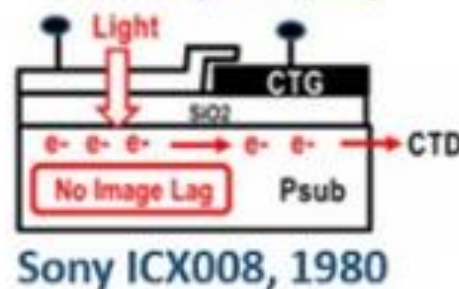
11 Conclusion

Historical development and research efforts of image sensors were reviewed in details. Image sensors and solar cells are both the photon detecting device (PPD) and operate with the same physical principle of photon energy to electron energy conversion.

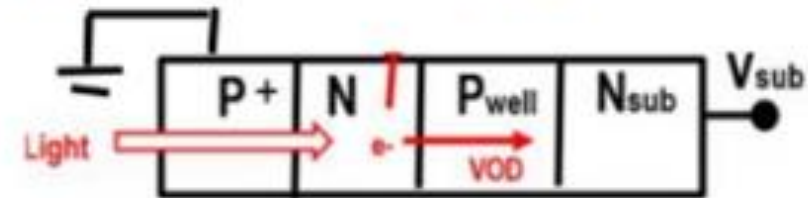
(1) N+P junction Photodiode in 1960s



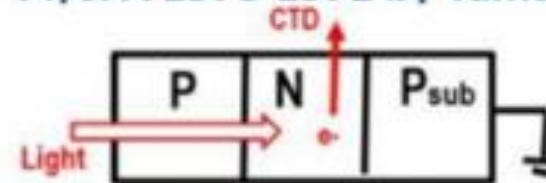
(2) Transparent Electrode CCD/MOS Photo Capacitor (1980)



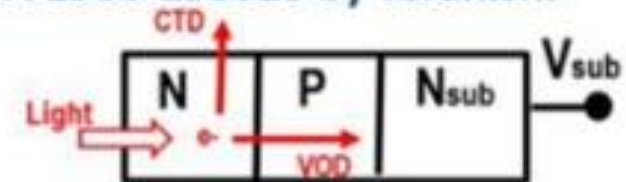
(3) JPA 1975-134985 by Hagiwara



(4) JPA 1978-1971 by Yamada



(5) JPA 1980-138026 by Teranishi



11 Conclusion

A typical classical image sensor was simply composed of a single N+P floating junction type photon detecting device (PDD) which has the serious image lag problem and moreover the short wave blue light sensitivity was not satisfactory and had a poor color reproduction capability for professional usage but used widely in consumer markets.

feature \ type	Classical N+Psub Photodiode	Surface Channel CCD	Buried Channel CCD	Yamada 1978 NPNsub	Teranishi 1980 PNPsub	Hagiwara 1975 PNPNsub
Blue Light Sensitivity	△	X	X	○	○	○
Low Image Lag	X	○	○	X	○	○
Surface Dark Current	○	X	X	X	○	○
Surface Trap Noise	○	X	○	X	○	○
Vertical OFD (VOD)	X	X	X	○	X	○
Electrical Shutter	X	X	X	X	X	○

11 Conclusion

Image sensors were studied and developed aggressively for the quest of high quality and performance. On the other hand, solar cells stay in the most primitive and simple form of a single N+P floating junction type photon detecting device (PDD) even now for the reason of the solar cell market size and the low cost of fabrication process.

feature \ type	Classical N+Psub Photodiode	Surface Channel CCD	Buried Channel CCD	Yamada 1978 NPNsub	Teranishi 1980 PNPsub	Hagiwara 1975 PNPNsub
Blue Light Sensitivity	△	X	X	○	○	○
Low Image Lag	X	○	○	X	○	○
Surface Dark Current	○	X	X	X	○	○
Surface Trap Noise	○	X	○	X	○	○
Vertical OFD (VOD)	X	X	X	○	X	○
Electrical Shutter	X	X	X	X	X	○

11 Conclusion

In 1970 CCD/MOS dynamic capacitor type both PDD and CTD were invented by Boyle and Smith in Bell Lab. However, because the CCD type PDD is made of a series of MOS type dynamic photo capacitors with the metal electrodes on the top, the light cannot pass thru the metal electrodes. The CCD type PDD had a very poor light sensitivity.

feature \ type	Classical N+Psub Photodiode	Surface Channel CCD	Buried Channel CCD	Yamada 1978 NPNsub	Teranishi 1980 PNPsub	Hagiwara 1975 PNPNsub
Blue Light Sensitivity	△	X	X	○	○	○
Low Image Lag	X	○	○	X	○	○
Surface Dark Current	○	X	X	X	○	○
Surface Trap Noise	○	X	○	X	○	○
Vertical OFD (VOD)	X	X	X	○	X	○
Electrical Shutter	X	X	X	X	X	○

11 Conclusion

The CCD type PDD and CTD both have no image lag problem since they have the complete charge transfer efficiency of 99.999% for the analog TV era. But the classical N+P floating single junction type PDD has the serious image lag.

feature \ type	Classical N+Psub Photodiode	Surface Channel CCD	Buried Channel CCD	Yamada 1978 NPNsub	Teranishi 1980 PNPsub	Hagiwara 1975 PNPNsub
Blue Light Sensitivity	△	X	X	○	○	○
Low Image Lag	X	○	○	X	○	○
Surface Dark Current	○	X	X	X	○	○
Surface Trap Noise	○	X	○	X	○	○
Vertical OFD (VOD)	X	X	X	○	X	○
Electrical Shutter	X	X	X	X	X	○

11 Conclusion

Sony used the CCD type PDD once in 1980 with the thin polysilicon electrodes to have a fair blue light sensitivity. But that was the only case. Since then, the CCD type PDD with the poor light sensitivity was never used in image sensors.

feature \ type	Classical N+Psub Photodiode	Surface Channel CCD	Buried Channel CCD	Yamada 1978 NPNsub	Teranishi 1980 PNPsub	Hagiwara 1975 PNPNsub
Blue Light Sensitivity	△	X	X	○	○	○
Low Image Lag	X	○	○	X	○	○
Surface Dark Current	○	X	X	X	○	○
Surface Trap Noise	○	X	○	X	○	○
Vertical OFD (VOD)	X	X	X	○	X	○
Electrical Shutter	X	X	X	X	X	○

11 Conclusion

On the other hand, the CCD type CTD was used intensively. The CCD type CTD had an excellent charge transfer efficiency of 99.999% which was good enough for the analog TV era during 1980s and 1990s.

feature \ type	Classical N+Psub Photodiode	Surface Channel CCD	Buried Channel CCD	Yamada 1978 NPNsub	Teranishi 1980 PNPsub	Hagiwara 1975 PNPsub
Blue Light Sensitivity	△	X	X	○	○	○
Low Image Lag	X	○	○	X	○	○
Surface Dark Current	○	X	X	X	○	○
Surface Trap Noise	○	X	○	X	○	○
Vertical OFD (VOD)	X	X	X	○	X	○
Electrical Shutter	X	X	X	X	X	○

11 Conclusion

A modern CMOS image sensor is also composed of three parts, a PDD, a CTD and an output circuit. However, a modern CMOS image sensors now has much improved parts.

feature \ type	Classical N+Psub Photodiode	Surface Channel CCD	Buried Channel CCD	Yamada 1978 NPNsub	Teranishi 1980 PNPsub	Hagiwara 1975 PNPNsub
Blue Light Sensitivity	△	X	X	○	○	○
Low Image Lag	X	○	○	X	○	○
Surface Dark Current	○	X	X	X	○	○
Surface Trap Noise	○	X	○	X	○	○
Vertical OFD (VOD)	X	X	X	○	X	○
Electrical Shutter	X	X	X	X	X	○

11 Conclusion

Both the single N+P floating junction type PDD and the CCD/MOS type PDD are now completely replaced by the double and triple dynamic junction type PDD.

feature \ type	Classical N+Psub Photodiode	Surface Channel CCD	Buried Channel CCD	Yamada 1978 NPNsub	Teranishi 1980 PNPsub	Hagiwara 1975 PNPNsub
Blue Light Sensitivity	△	X	X	○	○	○
Low Image Lag	X	○	○	X	○	○
Surface Dark Current	○	X	X	X	○	○
Surface Trap Noise	○	X	○	X	○	○
Vertical OFD (VOD)	X	X	X	○	X	○
Electrical Shutter	X	X	X	X	X	○

11 Conclusion

The double and triple dynamic junction type PDD with a vertical overflow drain (VOD) function was originally invented by Yoshiaki Hagiwara in 1975, with the completely mechanical free shutter function, realizing high speed action pictures.

feature \ type	Classical N+Psub Photodiode	Surface Channel CCD	Buried Channel CCD	Yamada 1978 NPNsub	Teranishi 1980 PNPsub	Hagiwara 1975 PNPNsub
Blue Light Sensitivity	△	X	X	○	○	○
Low Image Lag	X	○	○	X	○	○
Surface Dark Current	○	X	X	X	○	○
Surface Trap Noise	○	X	○	X	○	○
Vertical OFD (VOD)	X	X	X	○	X	○
Electrical Shutter	X	X	X	X	X	○

11 Conclusion

The CCD type CTD was also replaced completely by the in pixel source follower active circuit type CTD, which was originally invented by Peter Noble way back in 1969.

feature \ type	Classical N+Psub Photodiode	Surface Channel CCD	Buried Channel CCD	Yamada 1978 NPNsub	Teranishi 1980 PNPsub	Hagiwara 1975 PNPNsub
Blue Light Sensitivity	△	X	X	○	○	○
Low Image Lag	X	○	○	X	○	○
Surface Dark Current	○	X	X	X	○	○
Surface Trap Noise	○	X	○	X	○	○
Vertical OFD (VOD)	X	X	X	○	X	○
Electrical Shutter	X	X	X	X	X	○

11 Conclusion

Modern image sensors with CMOS type CTD also include the in pixel correlation double sampling (CDS) circuit technique invented by M. White which was already used in early 1970s intensively in the output circuit stage of CCD type CTD.

feature \ type	Classical N+Psub Photodiode	Surface Channel CCD	Buried Channel CCD	Yamada 1978 NPNsub	Teranishi 1980 PNPsub	Hagiwara 1975 PNPNsub
Blue Light Sensitivity	△	X	X	○	○	○
Low Image Lag	X	○	○	X	○	○
Surface Dark Current	○	X	X	X	○	○
Surface Trap Noise	○	X	○	X	○	○
Vertical OFD (VOD)	X	X	X	○	X	○
Electrical Shutter	X	X	X	X	X	○

11 Conclusion

The modern image sensors also include the in pixel Global Shutter Buffer Memory originally invented by Yoshiaki Hagiwara in 1975.

feature \ type	Classical N+Psub Photodiode	Surface Channel CCD	Buried Channel CCD	Yamada 1978 NPNsub	Teranishi 1980 PNPsub	Hagiwara 1975 PNPNsub
Blue Light Sensitivity	△	X	X	○	○	○
Low Image Lag	X	○	○	X	○	○
Surface Dark Current	○	X	X	X	○	○
Surface Trap Noise	○	X	○	X	○	○
Vertical OFD (VOD)	X	X	X	○	X	○
Electrical Shutter	X	X	X	X	X	○

11 Conclusion

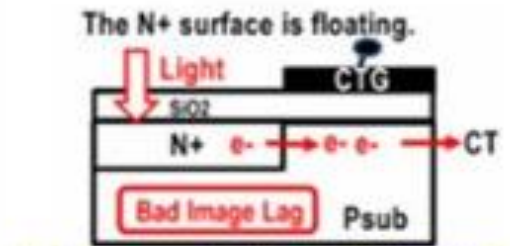
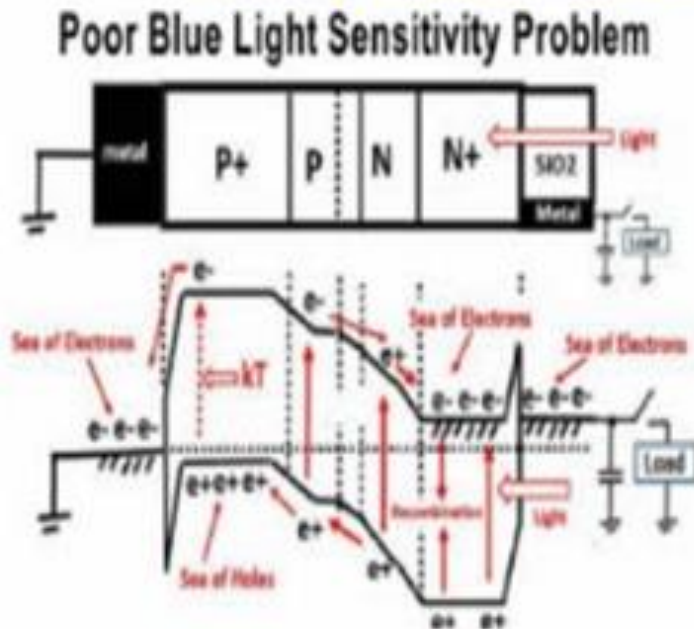
The modern image sensors also include the in column ADC and the CMOS output circuits, owing to the great advancement of CMOS LSI fabrication technology, following the Moore's law of MOS process scaling rule, by constant efforts of more than 50 years and still now evolving by the recent Multi Chip 3D Integration Technology.

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Blue Light Sensitivity	△	X	X	○	○	○
Low Image Lag	X	○	○	X	○	○
Surface Dark Current	○	X	X	X	○	○
Surface Trap Noise	○	X	○	X	○	○
Vertical OFD (VOD)	X	X	X	○	X	○
Electrical Shutter	X	X	X	X	X	○

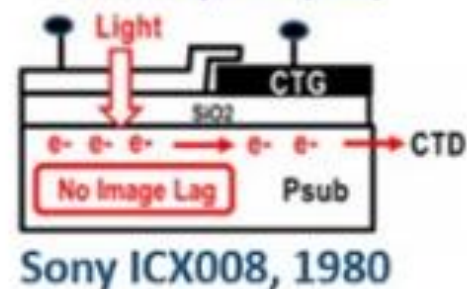
11 Conclusion

The digital CMOS video cameras, with all solid state, film free, mechanical parts free, high definition and low power features, now transformed the image sensor world from an analog life style to a digital life style completely.

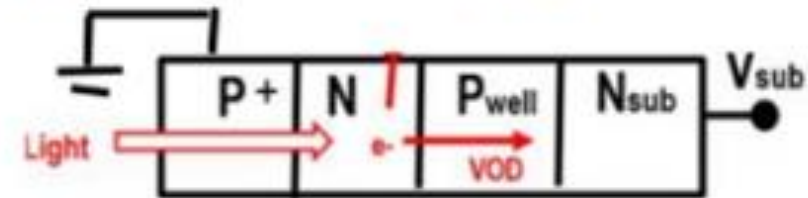
(1) N+P junction Photodiode in 1960s



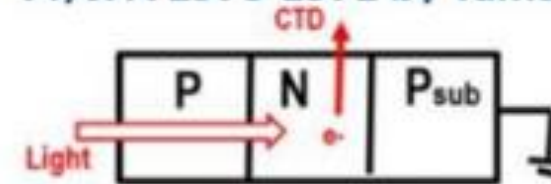
(2) Transparent Electrode CCD/MOS Photo Capacitor (1980)



(3) JPA 1975-134985 by Hagiwara



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(5) JPA 1980-138026 by Teranishi

